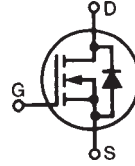


Polar™ Power MOSFETs HiPerFET™

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

IXFV52N30P
IXFV52N30PS
IXFH52N30P

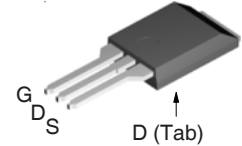


$$\begin{aligned} V_{DSS} &= 300V \\ I_{D25} &= 52A \\ R_{DS(on)} &\leq 73m\Omega \\ t_{rr} &\leq 200ns \end{aligned}$$

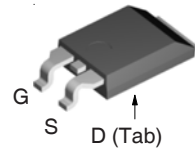
Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	300	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	300	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	52	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	150	A
I_A	$T_C = 25^\circ C$	52	A
E_{AS}	$T_C = 25^\circ C$	1	J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	10	V/ns
P_D	$T_C = 25^\circ C$	400	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-247)	1.13/10	Nm/lb.in
F_c	Mounting Force (PLUS220)	11..65/2.5..14.6	N/lb
Weight	PLUS220 & PLUS220SMD	4	g
	TO-247	6	g

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	300		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4mA$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$			25 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			73 m Ω

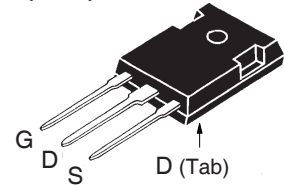
PLUS220 (IXFV)



PLUS220SMD (IXFV_S)



TO-247 (IXFH)



G = Gate D = Drain
S = Source Tab = Drain

Features

- Fast Intrinsic Rectifier
- Avalanche Rated
- Low $R_{DS(on)}$ and Q_G
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

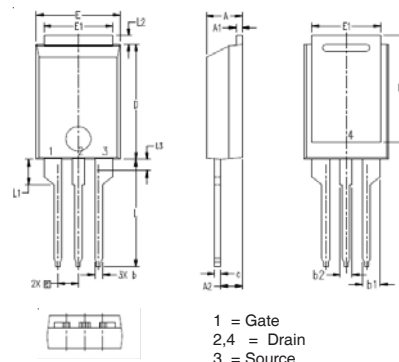
- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}, I_D = 0.5 \cdot I_{D25}$, Note 1	20	30	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		3490	pF
C_{oss}			550	pF
C_{rss}			130	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 52\text{A}$ $R_G = 4\Omega$ (External)		24	ns
t_r			22	ns
$t_{d(off)}$			60	ns
t_f			20	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		110	nC
Q_{gs}			25	nC
Q_{gd}			53	nC
R_{thJC}	(TO-247 & PLUS220)			0.31 $^\circ\text{C/W}$
R_{thCS}		0.25		$^\circ\text{C/W}$

Source-Drain Diode		Characteristic Values		
$T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			52 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			150 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 25\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$		160	200 ns
Q_{RM}			800	nC
I_{RM}			7	A

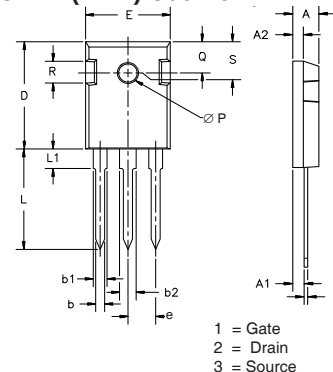
Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

PLUS220 (IXFV) Outline



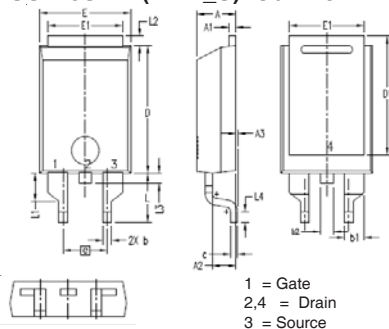
SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.028	.035	0.70	0.90
A2	.098	.118	2.50	3.00
b	.035	.047	0.90	1.20
b1	.080	.095	2.03	2.41
b2	.054	.064	1.37	1.63
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D1	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E1	.331	.346	8.40	8.80
e	.100	BSC	2.54	BSC
L	.512	.551	13.00	14.00
L1	.118	.138	3.00	3.50
L2	.035	.051	0.90	1.30
L3	.047	.059	1.20	1.50

TO-247 (IXFH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A1	2.2	2.54	.087	.102
A2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b1	1.65	2.13	.065	.084
b2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

PLUS220SMD (IXFV S) Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.028	.035	0.70	0.90
A2	.098	.118	2.50	3.00
A3	.000	.010	0.00	0.25
b	.035	.047	0.90	1.20
b1	.080	.095	2.03	2.41
b2	.054	.064	1.37	1.63
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D1	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E1	.331	.346	8.40	8.80
e	.100	BSC	2.54	BSC
L	.512	.551	13.00	14.00
L1	.118	.138	3.00	3.50
L2	.035	.051	0.90	1.30
L3	.047	.059	1.20	1.50
L4	.039	.059	1.00	1.50

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338 B2
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

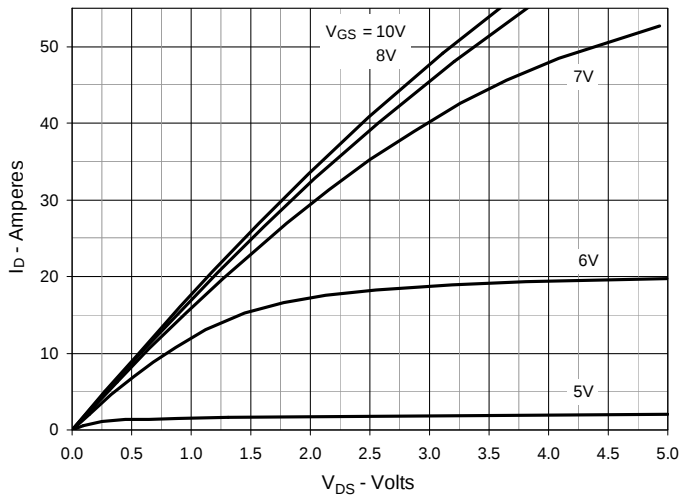


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

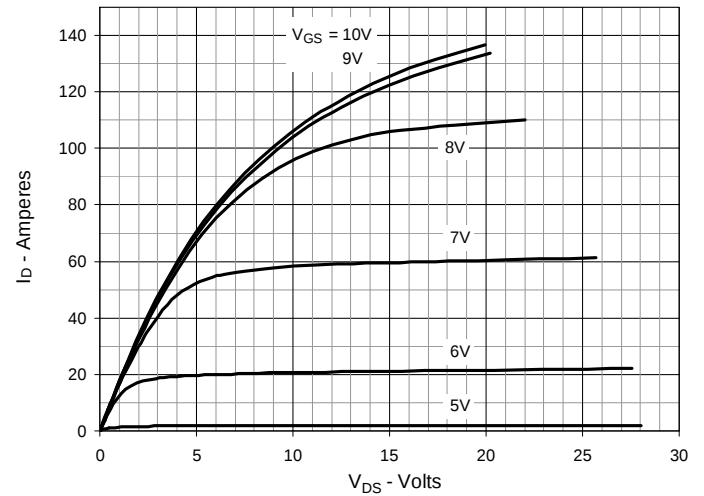


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

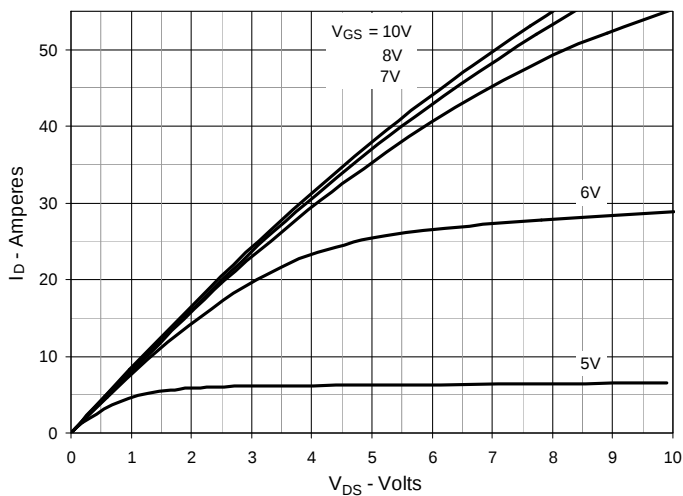


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 26\text{A}$ Value vs. Junction Temperature

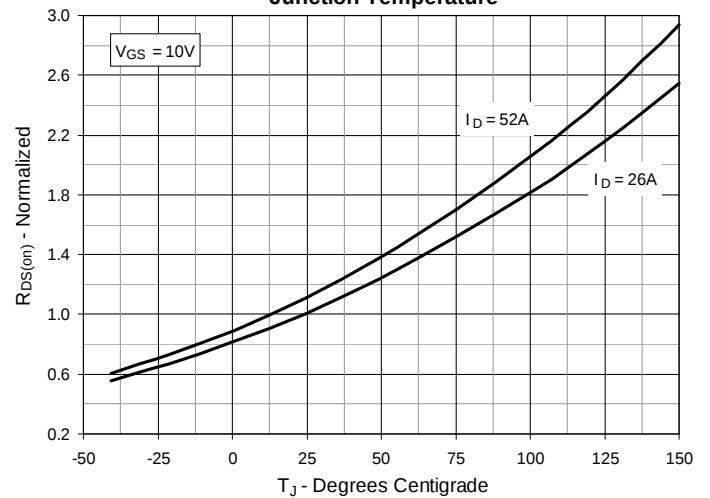


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 26\text{A}$ Value vs. Drain Current

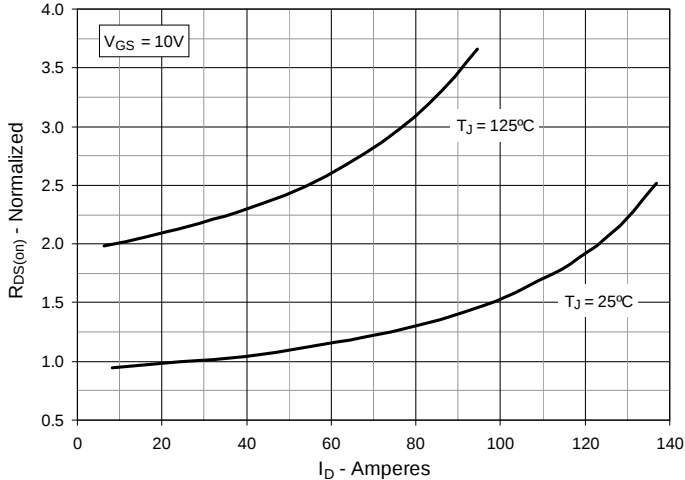


Fig. 6. Maximum Drain Current vs. Case Temperature

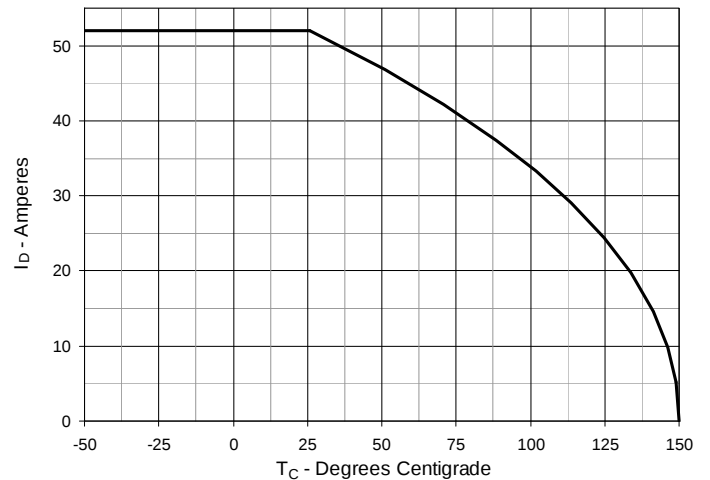


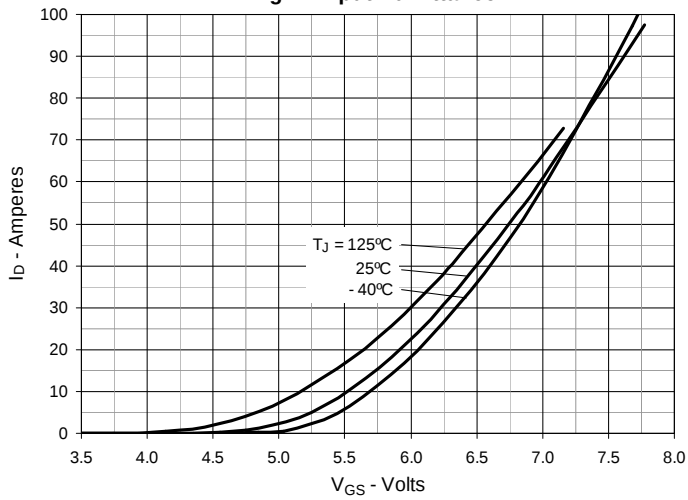
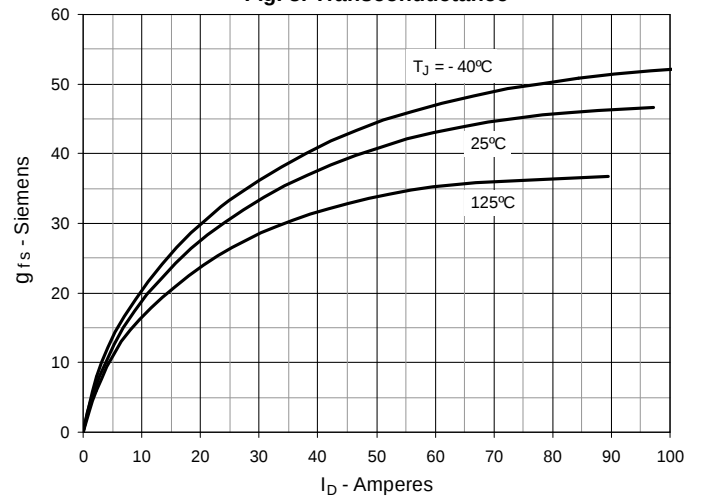
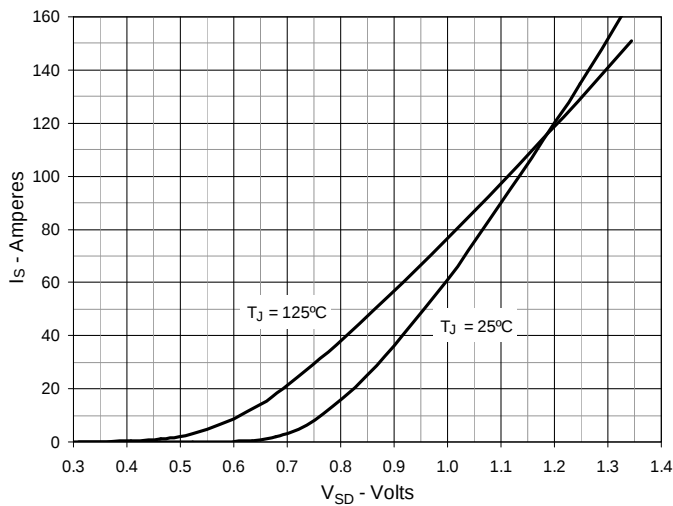
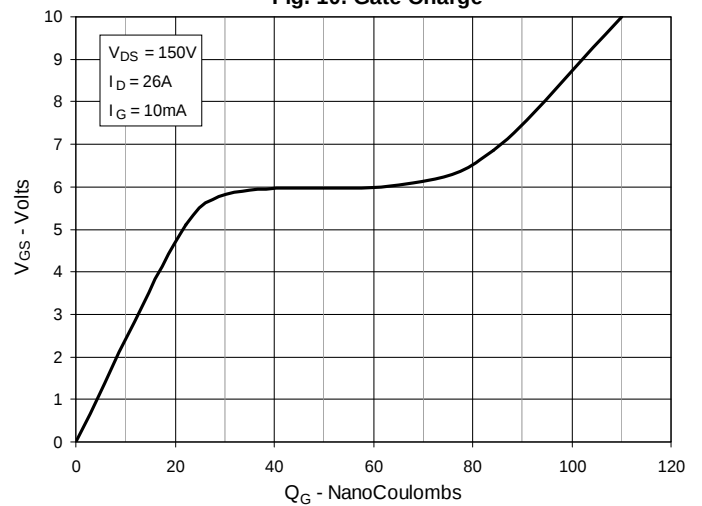
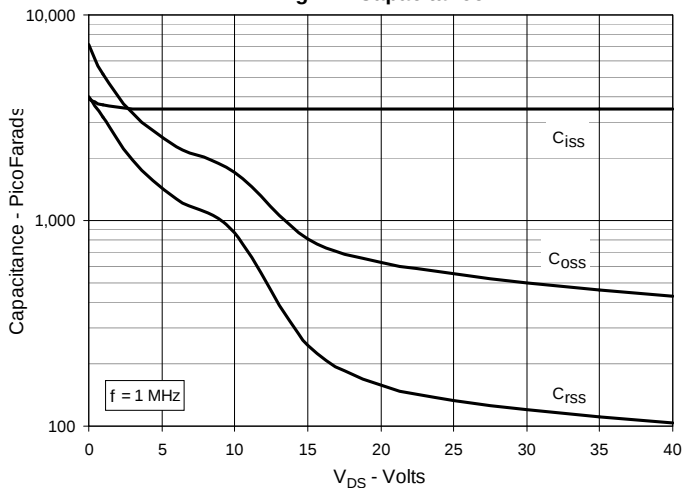
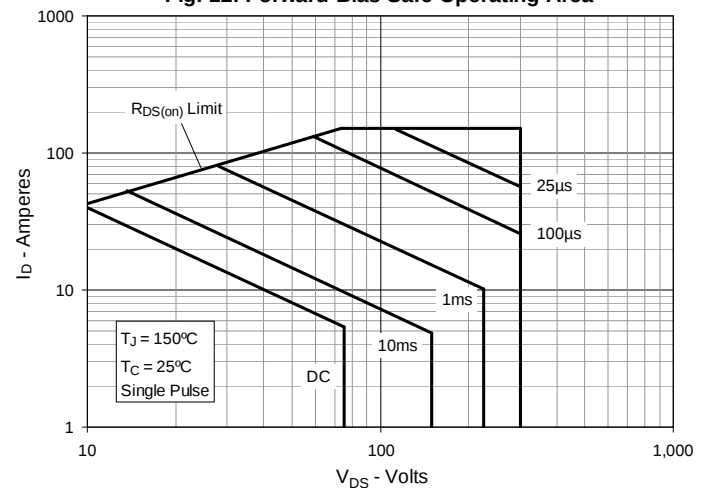
Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Forward-Bias Safe Operating Area


Fig. 13. Maximum Transient Thermal Impedance

